

# **BC517**

## **NPN Darlington Transistor**

- This device is designed for applications requiring extremely high current gain at currents to 1.0A.
- Sourced from process 05.



1. Collector 2. Base 3. Emitter

## Absolute Maximum Ratings \* Ta = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
I <sub>C</sub>	Collector Current - Continuous	1.2	А
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 ~ 150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may impaired.

#### NOTES:

## **Electrical Characteristics** $T_a = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Max	Units	
Off Characte	Off Characteristics					
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage *	$I_C = 2.0 \text{mA}, I_B = 0$	30		V	
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	40		V	
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 100nA, I <sub>C</sub> = 0	10		V	
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = 30V, I <sub>E</sub> = 0		100	nA	
On Characteristics *						
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 2.0V, I_{C} = 20mA$	30,000			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 100mA, I <sub>B</sub> = 0.1mA		1	V	
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_C = 10mA, V_{CE} = 5.0V$		1.4	V	

### Thermal Characteristics T<sub>a</sub> = 25°C unless otherwise noted

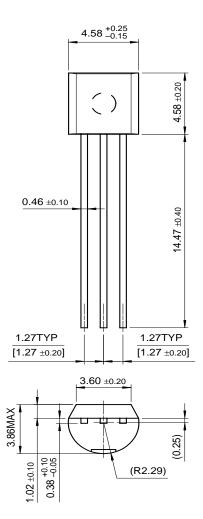
Symbol	Parameter	Value	Units
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

<sup>1.</sup> These ratings are based on a maximum junction temperature of 150 degrees C.

<sup>2.</sup> These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## **Mechanical Dimensions**

TO-92





Dimensions in Millimeters

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